

Amendments to the Claims:

Claims 1 and 8 have been amended herein. Claims 13-20 have been added. Please note that all claims currently pending and under consideration in the referenced application are shown below. Please enter these claims as amended. This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently Amended) A column line structure for use in a cathode assembly of a field emission device, comprising:
an elongated conductive structure;
a resistive layer disposed on a top surface of the elongated conductive structure and extending over at least a portion of one or more side surfaces thereof; and
an insulative layer disposed over a top surface of the resistive layer having outer edges substantially aligned and having side surfaces substantially coincident with side surfaces of the resistive layer.
2. (Previously Presented) The column line structure of Claim 1 wherein the elongated conductive structure comprises metal.
3. (Previously Presented) The column line structure of Claim 1 wherein the elongated conductive structure comprises aluminum.
4. (Previously Presented) The column line structure of Claim 1 wherein the resistive layer comprises silicon.
5. (Previously Presented) The column line structure of Claim 1 wherein the insulative layer comprises silicon oxide.

6. (Previously Presented) The column line structure of Claim 1 wherein the insulative layer comprises silicon nitride.

7. (Previously Presented) The column line structure of Claim 1 wherein the insulative layer has a thickness of about 1000 Å.

8. (Currently Amended) A field emission device, comprising a cathode assembly and an anode assembly assembled with the cathode assembly, wherein the cathode assembly includes an addressing matrix comprising multiple row lines elevationally disposed above column lines, the column lines having an insulating layer disposed thereon over a top surface thereof, wherein the insulating layer substantially exactly overlies the column lines, and substantially conforming to lateral dimensions thereof.

9. (Previously Presented) The field emission device of claim 8, wherein the column lines include at least one conductive layer and a resistive layer disposed over at least a top surface of the at least one conductive layer.

10. (Previously Presented) The field emission device of claim 9, wherein the resistive layer extends over at least a portion of at least one side surface of the at least one conductive layer.

11. (Previously Presented) The field emission device of claim 10, wherein the resistive layer extends over opposing side surfaces of the at least one conductive layer.

12. (Previously Presented) The field emission device of claim 1, wherein the resistive layer is disposed directly on the top surface of the elongated conductive structure.

13. (New) A field emission device, comprising:
a plurality of column line structures, each of the plurality of column line structures comprising:
an elongated conductive structure;
a resistive layer disposed on a top surface of the elongated conductive structure and
extending over at least a portion of one or more side surfaces thereof; and
an insulative layer disposed over a top surface of the resistive layer and having outer
edges substantially aligned with side surfaces of the resistive layer; and
a dielectric layer disposed over at least portions of the plurality of column line structures.

14. (New) The field emission device of Claim 13, wherein the elongated conductive structure comprises metal.

15. (New) The field emission device of Claim 13, wherein the elongated conductive structure comprises aluminum.

16. (New) The field emission device of Claim 13, wherein the resistive layer comprises silicon.

17. (New) The field emission device of Claim 13, wherein the insulative layer comprises silicon oxide.

18. (New) The field emission device of Claim 13, wherein the insulative layer comprises silicon nitride.

19. (New) The field emission device of Claim 13, wherein the insulative layer has a thickness of about 1000 Å.

20. (New) The field emission device of Claim 13, wherein the resistive layer is disposed directly on the top surface of the elongated conductive structure.